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(74) Agents: **MARTIN, Jean-Jacques** et al.; Cabinet Regim-
beau, 20, Rue De Chazelles, F-75847 Paris Cedex 17 (FR).

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(71) Applicant (for all designated States except US):
**S.O.I.TEC SILICON ON INSULATOR TECH-
NOLOGIES** [FR/FR]; Parc Technologique des Fontaines,
Chemin des Franques, F-38190 Bernin (FR).

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(72) Inventors; and

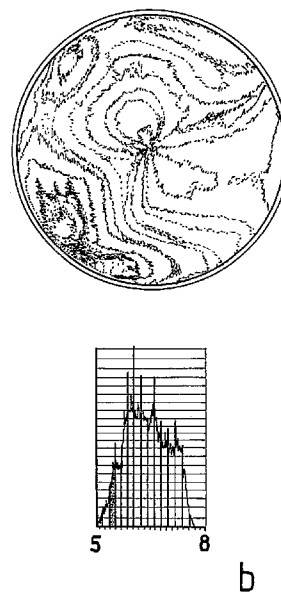
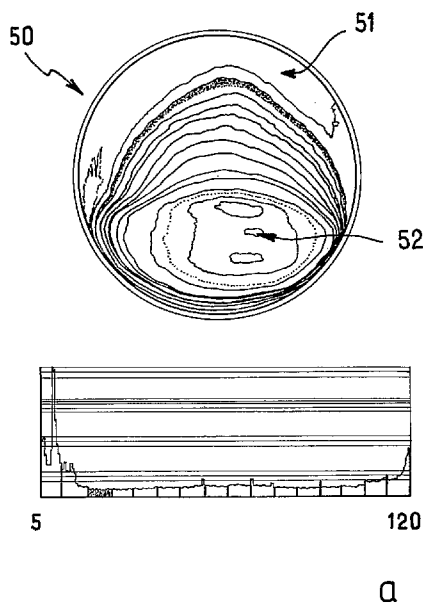
(75) Inventors/Applicants (for US only): **NEYRET, Eric**
[FR/FR]; 2, rue Lesdiguières, F-38360 Sassenage (FR).
ARENE, Emmanuel [FR/FR]; 1 Clos des Fraquières,
F-38330 Biviers (FR). **ECARNOT, Ludovic** [FR/FR]; 11,
rue de la Libération, F-38610 Gieres (FR).

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(54) Title: PROCESS FOR IMPROVING THE SURFACE ROUGHNESS OF A WAFER



(57) Abstract: The present invention relates to a process for reducing the roughness of the free surface of a semiconductor wafer, said process comprising a single annealing step for smoothing said free surface, said single annealing step being carried out as a RTA under an atmosphere of pure argon, characterized in that before the RTA the atmosphere of the annealing environment is purged in a controlled manner so as to establish a controlled purged atmosphere allowing reduction of preliminary pollutants on the wafer.

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